Supplementary Information to

Unexpected phosphorus doping routine of planar silicon nanowires for integrating CMOS logics

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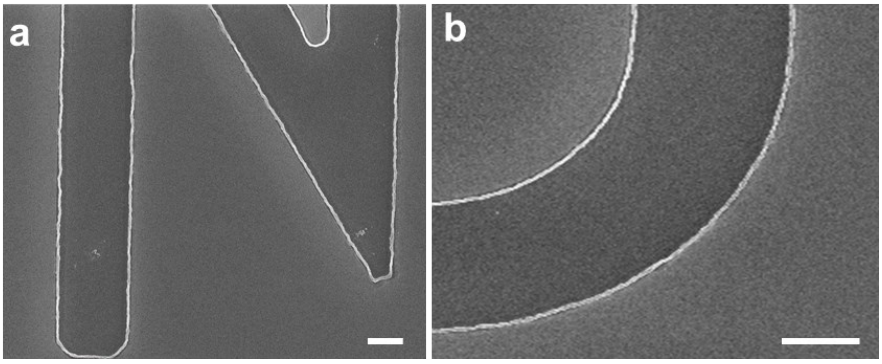

Fig. S1. Close SEM images of the ultralong n-type SiNWs grown along the curved or straight guiding edge lines. Scale bars are both for 2 μm.

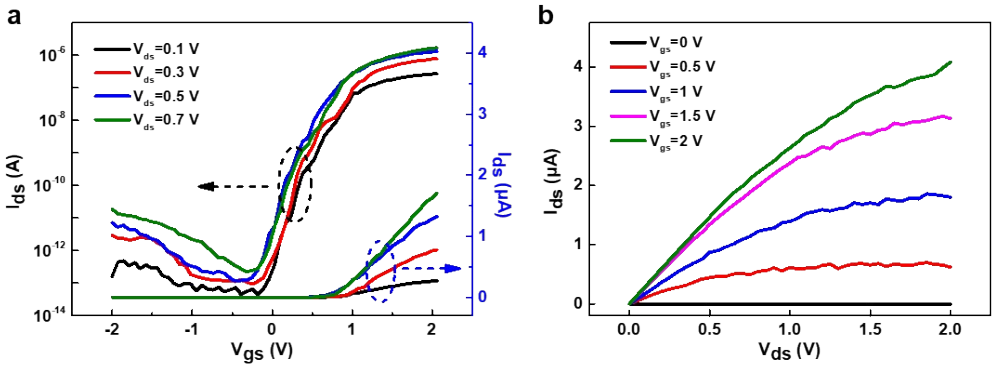

Fig. S2. Electrical properties of the n-type SiNW FETs. (a) presents the transfer curves under different V_{ds} biases, while the different output curves are shown in (b).